

**Vishay Siliconix** 

RoHS

COMPLIANT

HALOGEN

Available

# P-Channel 60 V (D-S) MOSFET

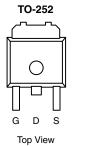
PRODUCT SUMMARY					
V <sub>DS</sub> (V)	<b>R<sub>DS(on)</sub> (</b> Ω <b>)</b>	I <sub>D</sub> (A) <sup>d</sup>	Q <sub>g</sub> (Typ)		
- 60	0.060 at V <sub>GS</sub> = - 10 V	- 19	26		
- 00	0.077 at $V_{GS}$ = - 4.5 V	- 16.8	20		

### FEATURES

- Halogen-free According to IEC 61249-2-21
  Definition
- TrenchFET<sup>®</sup> Power MOSFET
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC

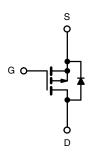
### **APPLICATIONS**

- High Side Switch for Full Bridge Converter
- DC/DC Converter for LCD Display





SUD19P06-60-GE3 (Lead (Pb)-free and Halogen free)



Ordering Information: SUD19P06-60-E3 (Lead (Pb)-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ( $T_A = 2$	25 °C, unless otherw	ise note)			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V <sub>DS</sub>	- 60	v	
Gate-Source Voltage	V <sub>GS</sub>	± 20	v		
Continuous Drain Current ( $T_{1}$ = 150 °C)	T <sub>C</sub> = 25 °C	1-	- 18.3		
$Commutous Drain Current (1) = 150^{\circ} C)$	T <sub>C</sub> = 125 °C	I <sub>D</sub>	- 8.19		
Pulsed Drain Current		I <sub>DM</sub>	- 30	- A	
Avalanche Current, Single Pulse	L = 0.1 mH	I <sub>AS</sub>	- 22		
Repetitive Avalanche Energy, Single Pulse <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	24.2	mJ	
Dawer Diasingtion	T <sub>C</sub> = 25 °C	P	38.5 <sup>c</sup>	w	
Power Dissipation	T <sub>A</sub> = 25 °C	P <sub>D</sub>	2.3 <sup>b, c</sup>	VV	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Marine Incelling to Angle South	t ≤ 10 s	R <sub>thJA</sub>	17	21	°C/W	
Maximum Junction-to-Ambient <sup>D</sup>	Steady State		45	55		
Maximum Junction-to-Case		R <sub>thJC</sub>	2.7	3.25		
Notes:			1	11		

a. Duty cycle  $\leq$  1 %.

b. When mounted on 1" square PCB (FR-4 material).

c. See SOA curve for voltage derating.

d. Based up on  $T_C = 25 \degree C$ .

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# SUD19P06-60

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Parameter	Symbol	Test Conditions	Min .	Тур.	Max.	Unit	
Static				-			
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 V$ , $I_{D} = -250 \mu A$	- 60			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$	- 1		- 3	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0$ V, $V_{GS} = \pm 20$ V			± 100	nA	
		$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}$			- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ = - 60 V, $V_{GS}$ = 0 V, $T_{J}$ = 125 °C			- 50	μA	
		$V_{DS}$ = - 60 V, $V_{GS}$ = 0 V, $T_{J}$ = 150 ° C			- 125		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = -5 V, V_{GS} = -10 V$	- 30			Α	
		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 10 A		0.048	0.060		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS}$ = - 10 V, I <sub>D</sub> = - 10 A, T <sub>J</sub> = 125 °C	0.		0.102	Ω	
Diam-Source On-State Resistance	''DS(on)	$V_{GS}$ = - 10 V, I <sub>D</sub> = - 10 A, T <sub>J</sub> = 150 °C			0.120		
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 5 A		0.061	0.077		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 10 A		22		S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			1140	1710	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$ , $V_{DS} = -25 V$ , f = 1 MHz		130			
Reverse Transfer Capacitance	C <sub>rss</sub>			90			
Total Gate Charge <sup>c</sup>	Qg			26	40	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = -30$ V, $V_{GS} = -10$ V, $I_{D} = -10$ A		4.5			
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			7		1	
Gate Resistance	Rg	f = 1 MHz		7		Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			8	15		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = - 30 V, $R_L$ = 3 $\Omega$		9	15	-	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$\rm I_D \cong$ - 19 A, $\rm V_{GEN}$ = - 10 V, $\rm R_g$ = 2.5 $\Omega$		65	100	ns	
Fall Time <sup>c</sup>	t <sub>f</sub>	]		30	45		
Drain-Source Body Diode and Characte	eristics (T <sub>C</sub> = 2	5 °C) <sup>b</sup>					
Continuous Current	I <sub>S</sub>				- 30		
Pulsed Current	I <sub>SM</sub>				- 30	A	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = - 19 A, V <sub>GS</sub> = 0 V		- 1	- 1.5	V	
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 19 A, di/dt = 100 A/μs		41	61	ns	

Notes:

a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

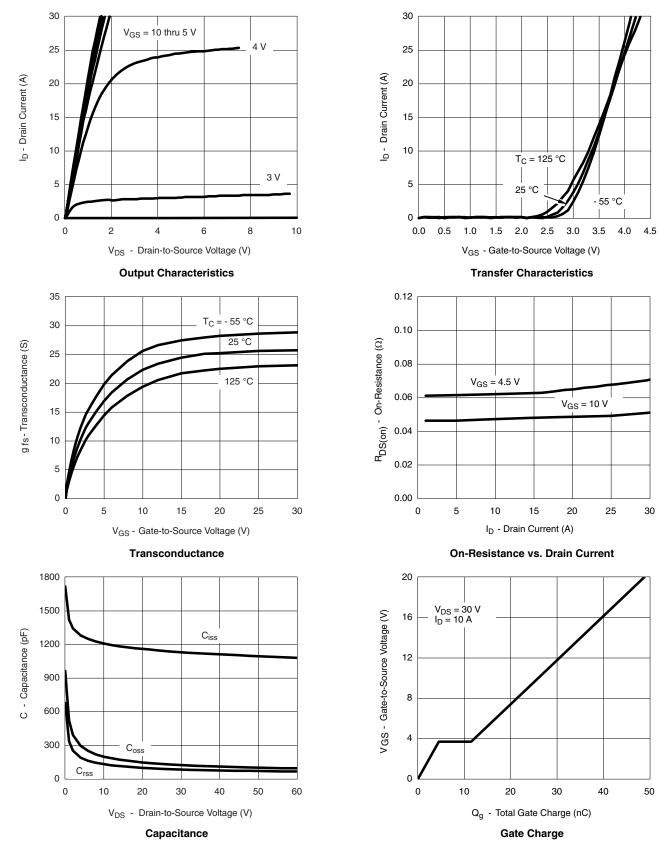
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



# SUD19P06-60

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### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



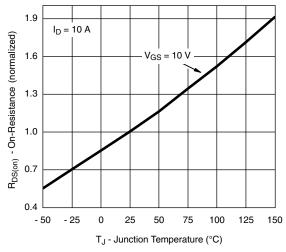
Document Number: 69253 S11-2132 Rev. B, 31-Oct-11 www.vishay.com

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# SUD19P06-60

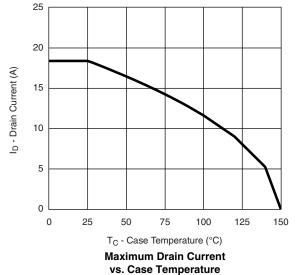
### **Vishay Siliconix**

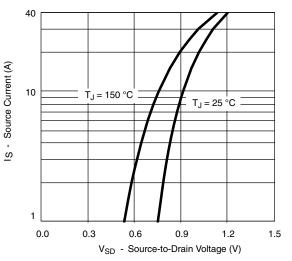
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



**On-Resistance vs. Junction Temperature** 

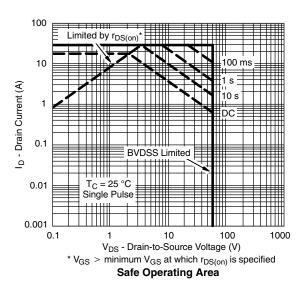


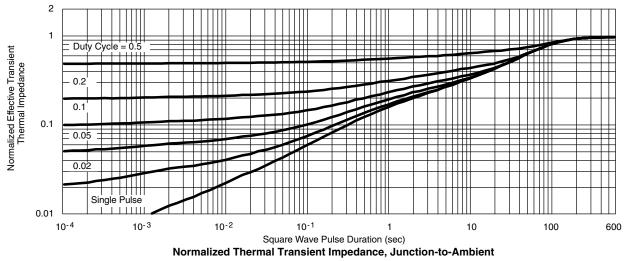




**ISHA** 

Source-Drain Diode Forward Voltage





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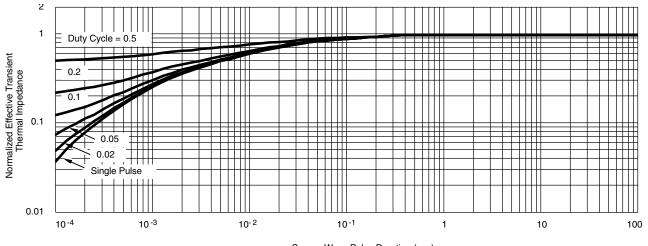
Document Number: 69253 S11-2132 Rev. B, 31-Oct-11



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### **THERMAL RATINGS**



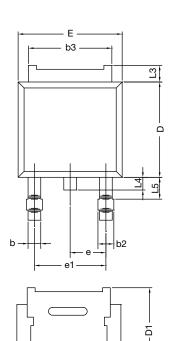
Square Wave Pulse Duration (sec)

Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?69253.







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**TO-252AA** Case Outline

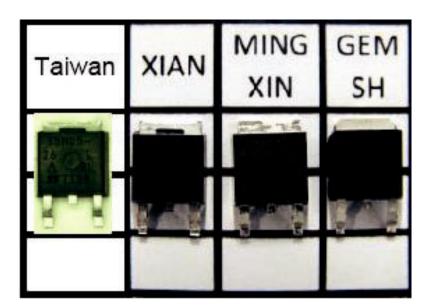
	MILLIMETERS		INC	HES
DIM.	MIN.	MAX.	MIN.	MAX.
А	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
С	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
Н	9.40	10.41	0.370	0.410
е	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060
ECN: T13-0359-Rev. O, 03-Jun-13 DWG: 5347				

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Notes

• Dimension L3 is for reference only.

• Xi'an, Mingxin, and GEM SH actual photo.



Revision: 03-Jun-13

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### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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